YJ Planar Fast Recovery Diode Die Specification

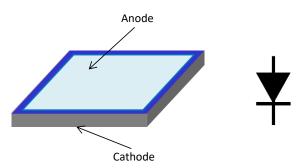
200V 10A, Fast recovery diode die based on silicon planar process Part No.: FRD10B200AS-290A

Main Products Characterstics • Average forward current: IF(AV) = 10A

• Maximum operating junction temperature: Tj = 150 °C

Planar Construction

· Top metal: Al



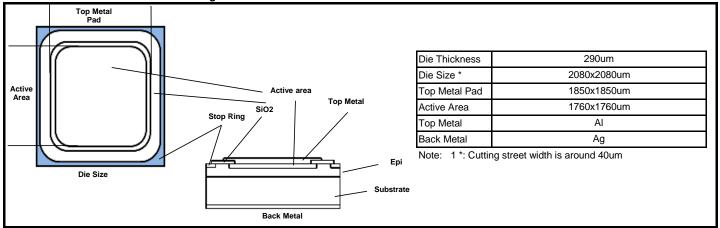
Maximum Ratings

Parameter	Symbol	Rating	
Repetitive peak reverse voltage	V_{RRM}	200V	
Average forward current	I _{F(AV)}	10A	
Non-repetitive peak surge current (tp = 8.3 ms, halfwave, 1 cycle)	I _{FSM}	100A	
Storage temperature range	T _{stg}	-40 to +150 °C	
Maximum operating junction temperature	T _j	150 °C	

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
Faranietei	Syllibol	Spec	Typical
Reverse breakdown voltage $I_R = 50$ uA	V_{BR}	220V	230V
Maximum forward voltage drop I_F = 10A, Pulse Test: tp = 380 µs, $ \delta \leqslant 2\% $	V _F	1.00V	0.92V
Reverse Recovery Time I _F =0.5A, I _R =1A, I _{rr} =0.25A	Trr	35ns	28ns
$\label{eq:maximum reverse current} \begin{split} \text{Maximum reverse current} & \ V_R = V_{RRM} \\ \text{Pulse Test: tp = 10 ms, } & \delta \leqslant 2\% \end{split}$	I _R	2uA	0.02uA

Device Schematics and Outline Drawing



Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly. All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.

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